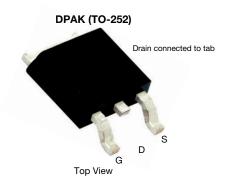


www.vishay.com

Vishay Siliconix

P-Channel 60 V (D-S) MOSFET

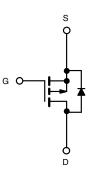


PRODUCT SUMMARY						
V _{DS} (V)	-60					
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.155					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.280					
Q _g typ. (nC)	12.5					
I _D (A)	-8.4					
Configuration	Single					

FEATURES

- TrenchFET® power MOSFETs
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





P-Channel MOSFET

ORDERING INFORMATION				
Package	DPAK (TO-252)			
Lead (Pb)-free and halogen-free	SUD08P06-155L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Gate-source voltage	V _{GS}	± 20	V		
Continuous drain ourrent (T = 150 °C)	T _C = 25 °C	1	-8.2		
Continuous drain current (T _J = 150 °C)	T _C = 100 °C	- I _D	-5.2		
Pulsed drain current	I _{DM}	-18	Α		
Continuing source current (diode conduction)	I _S	-8.4			
Avalanche current	I _{AS}	-12]		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	7.2	mJ	
Maximum navay discination	T _C = 25 °C	Б	20.8 ^a	W	
Maximum power dissipation	T _A = 25 °C	P_{D}	1.7 b		
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	20	25	°C/W	
	Steady state		62	75		
Junction-to-case		R _{thJC}	5	6		

Notes

- a. See SOA curve for voltage derating
- b. Surface mounted on 1" x 1" FR-4 board

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PARAMETER SYMBOL TEST COND		TEST CONDITIONS	MIN.	TYP. a	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-	-	V	
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1	-2	-	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{DS} = -60 V, V _{GS} = 0 V	-	-	-1	μΑ	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-50		
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 150 °C	-	-	-150		
On-state drain current b	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-10	-	-	Α	
		$V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$	-	0.125	0.155	Ω	
Drain-source on-state resistance b	В	V _{GS} = -10 V, I _D = -5 A, T _J = 125 °C	-	-	0.280		
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = -10 V, I _D = -5 A, T _J = 150 °C	-	-	0.350		
		V _{GS} = -4.5 V, I _D = -2 A	-	0.158	0.280		
Forward transconductance b	9 _{fs}	$V_{DS} = -15 \text{ V}, I_D = -5 \text{ A}$	-	8	-	S	
Dynamic							
Input capacitance	C _{iss}		-	450	-	pF	
Output capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	65	-		
Reverse transfer capacitance	C _{rss}		-	40	-		
Total gate charge	Q_g		-	12.5	19		
Gate-source charge	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -8.4 \text{ A}$	-	2.3	-	nC	
Gate-drain charge	Q _{gd}		-	3.2	-		
Gate resistance	R_g	f = 1 MHz	-	8	-	Ω	
Turn-on delay time c	t _{d(on)}		-	5	10		
Rise time ^c	t _r	$V_{DD} = -30 \text{ V}, R_1 = 3.57 \Omega$	-	14	25		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -8.4 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$	-	15	25	ns	
Fall time ^c	t _f		-	7	12		
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C) ^b					
Pulsed current	I _{SM}		-	-	-20	Α	
Forward voltage b	V _{SD}	I _F = -2 A, V _{GS} = 0 V	-	-0.9	-1.3	V	
Reverse recovery time	t _{rr}	1 0 0 1:/-14 100 0 / -	-	50	80	ns	
Reverse recovery time	Q _{rr}	I _F = -8 A, di/dt = 100 A/μs	-	80	120	nC	

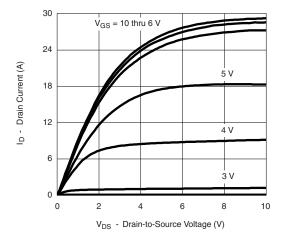
Notes

- a. Guaranteed by design, not subject to production testing
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. Independent of operating temperature

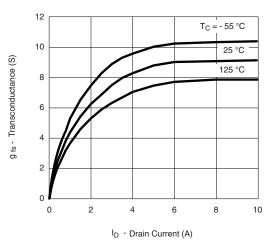
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



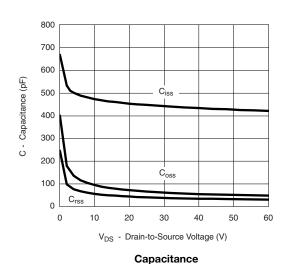
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

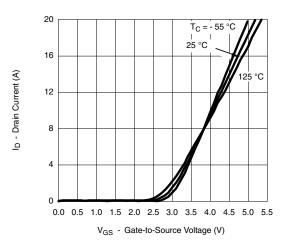


Output Characteristics

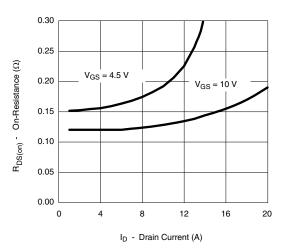


Transconductance

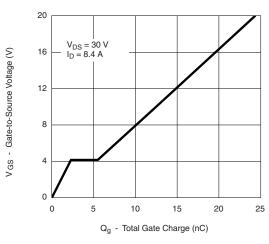




Transfer Characteristics

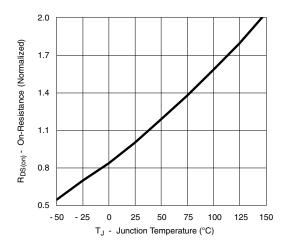


On-Resistance vs. Drain Current

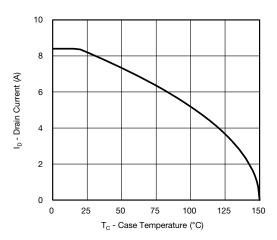




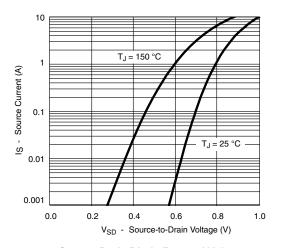
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



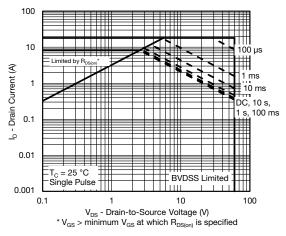
On-Resistance vs. Junction Temperature



Drain Current vs. Case Temperature



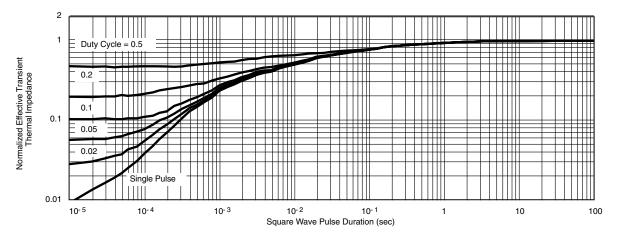
Source-Drain Diode Forward Voltage



Safe Operating Area

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



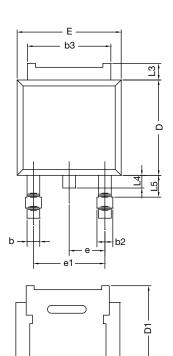
Normalized Thermal Transient Impedance, Junction-to-Case

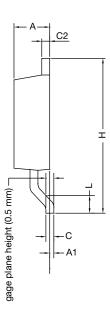
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TO-252AA Case Outline





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	2.28 BSC		BSC	
e1	4.56 BSC		0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T16-0236-Rev. P, 16-May-16					

DWG: 5347

Notes

• Dimension L3 is for reference only.

Revision: 16-May-16 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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ATTLICATION NOT



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